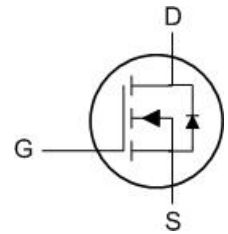
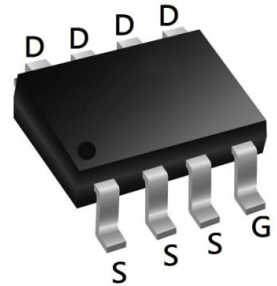


**Product Summary**

<b>BVDSS</b>	<b>RDSON</b>	<b>ID</b>
20V	8mΩ	12.0A

**SOP8 Pin Configuration**



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	12.0	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	7.0	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	34	A
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	3	W
$P_D@T_A=70^\circ C$	Total Power Dissipation <sup>3</sup>	0.86	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

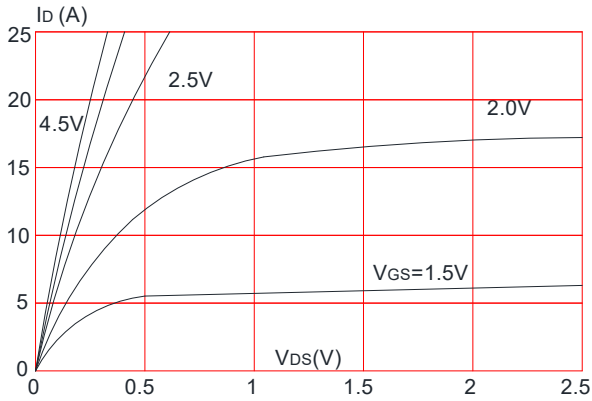
Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	100	$^\circ C/W$

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

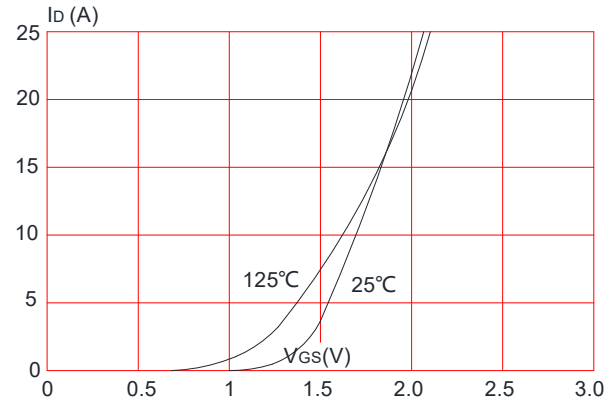
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=4.5V, I_D=15A$	-	8	11.2	m $\Omega$
		$V_{GS}=2.5V, I_D=10A$	-	11.7	17.5	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	1000	-	pF
$C_{oss}$	Output Capacitance		-	182	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	164	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=15A,$ $V_{GS}=4.5V$	-	15	-	nC
$Q_{gs}$	Gate-Source Charge		-	2	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	5.2	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=15A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	9	-	ns
$t_r$	Turn-on Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
$t_f$	Turn-off Fall Time		-	14	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	120	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V

## Typical Performance Characteristics

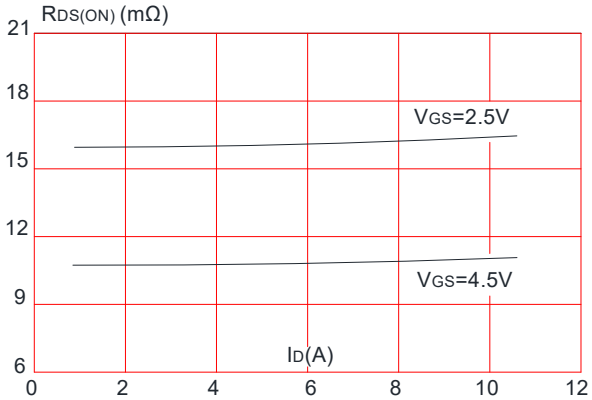
**Figure 1: Output Characteristics**



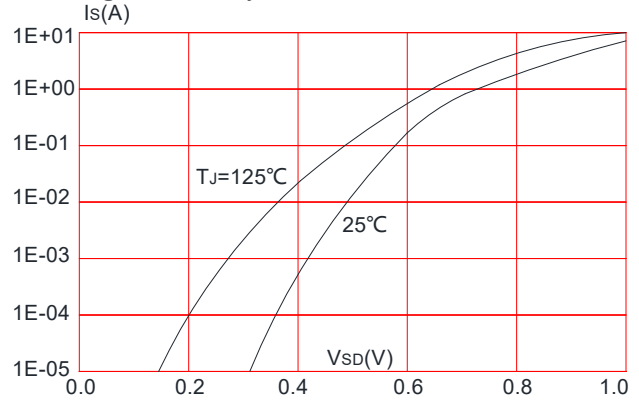
**Figure 2: Typical Transfer Characteristics**



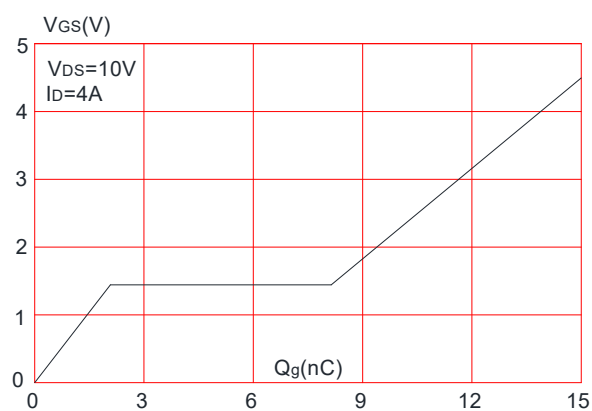
**Figure 3: On-resistance vs. Drain Current**



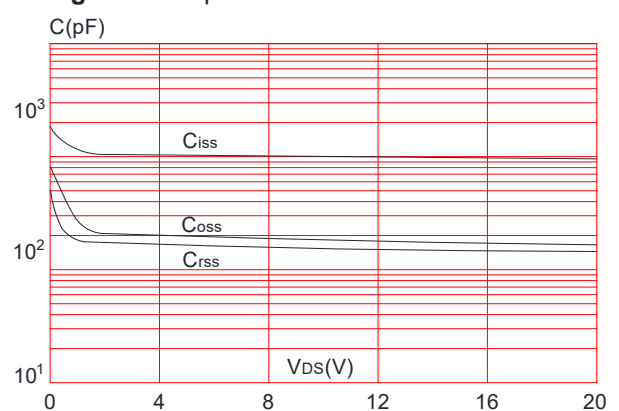
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

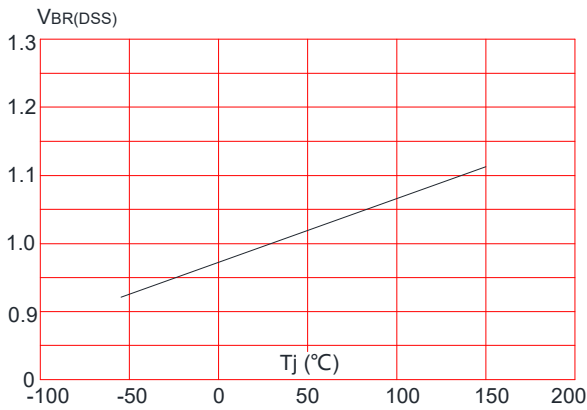


**Figure 6: Capacitance Characteristics**

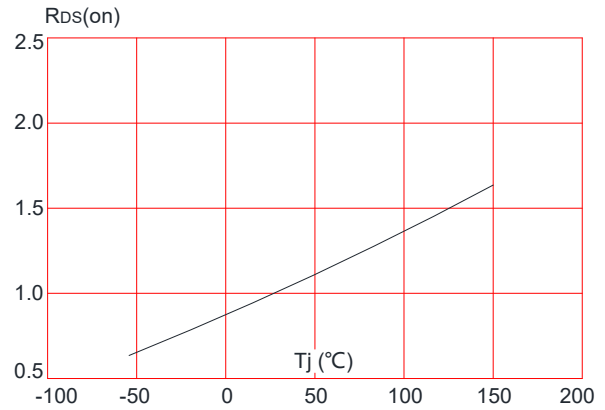


N-Ch 20V Fast Switching MOSFETs

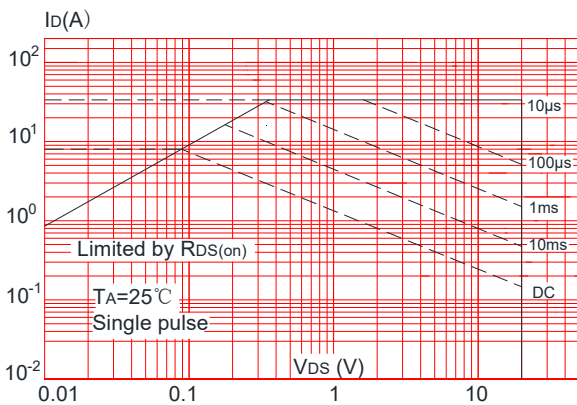
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



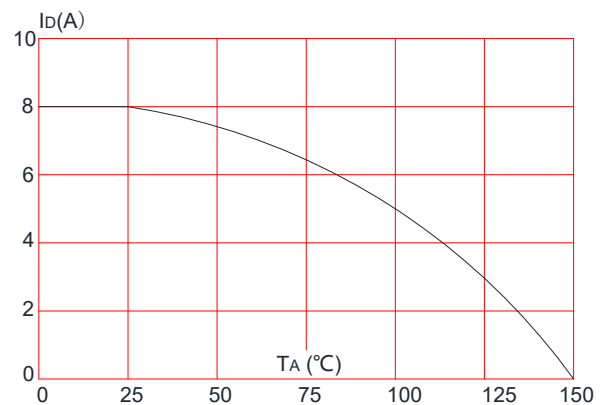
**Figure 8:** Normalized on Resistance vs. Junction Temperature



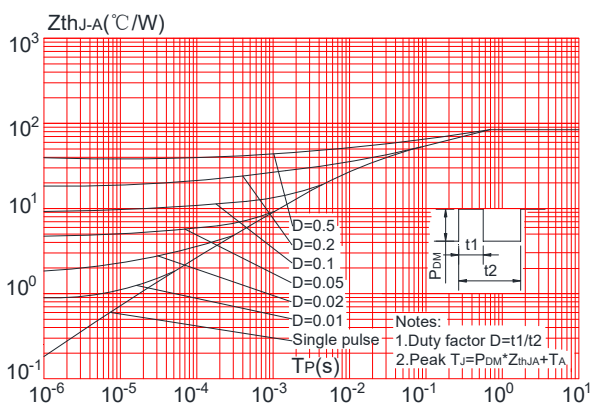
**Figure 9:** Maximum Safe Operating Area



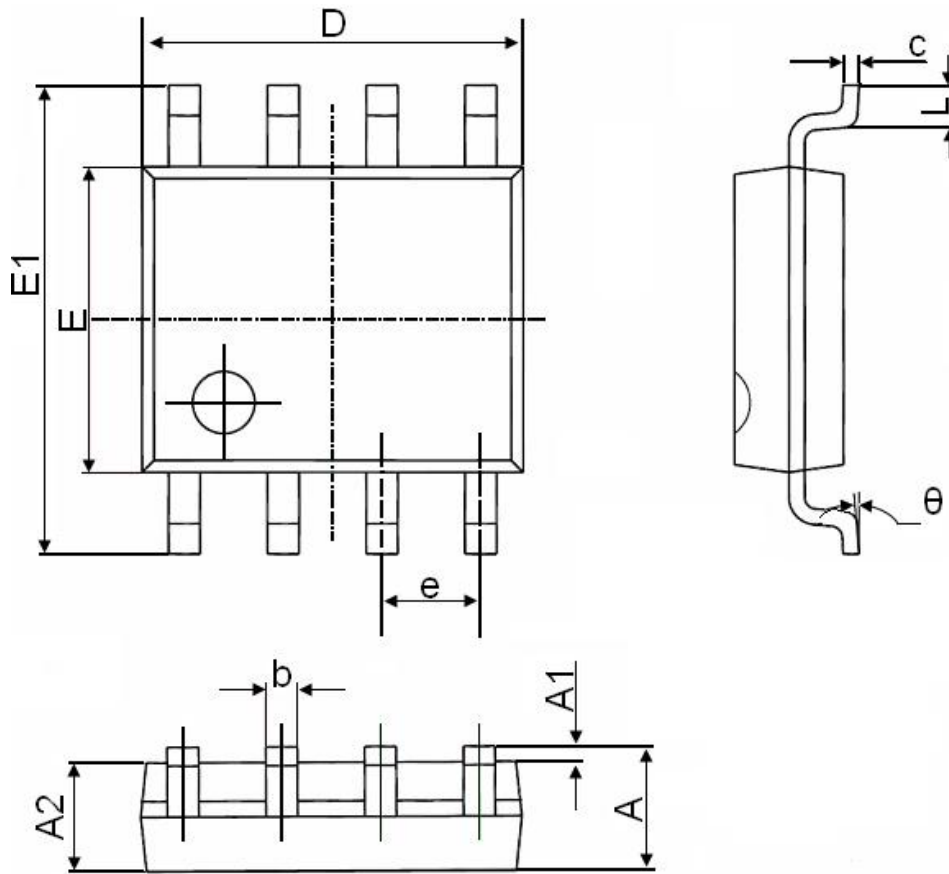
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°